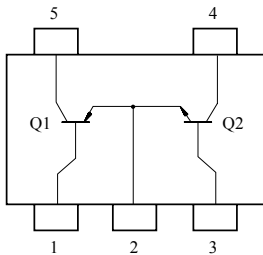


### GENERAL PURPOSE APPLICATION.

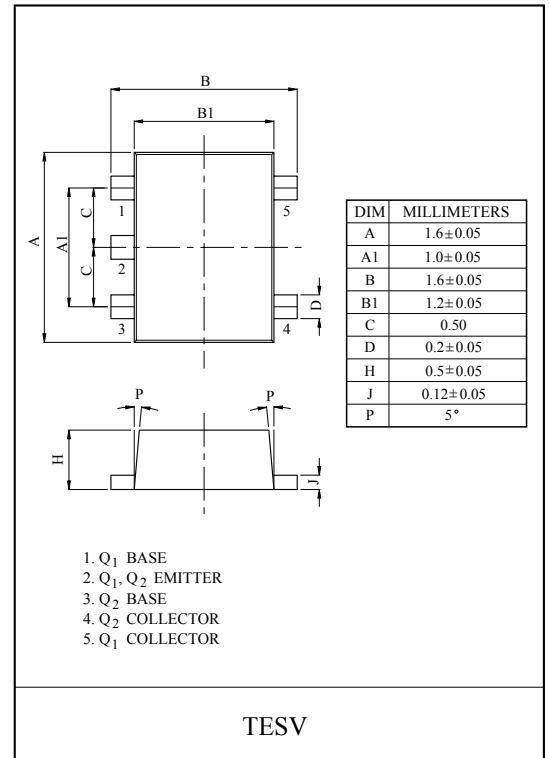
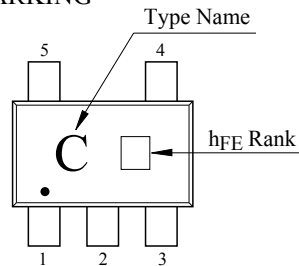
### FEATURES

- Including two devices in TESV.  
(Thin Extreme Super mini type with 5 pin)
- Simplify circuit design.
- Reduce a quantity of parts and manufacturing process.

EQUIVALENT CIRCUIT(TOP VIEW)



MARKING



### Q1 MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	-50	V
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-150	mA
Base Current	$I_B$	-30	mA

### Q2 MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	60	V
Collector-Emitter Voltage	$V_{CEO}$	50	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	150	mA
Base Current	$I_B$	30	mA

### Q1 Q2 MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector Power Dissipation	$P_C^*$	200	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_{stg}$	-55 ~ 150	°C

\* Total Rating.

# KTX201E

## Q<sub>1</sub> ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT.
Collector Cut-off Current	I <sub>CB0</sub>	V <sub>CB</sub> =-50V, I <sub>E</sub> =0	-	-	-0.1	μA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0	-	-	-0.1	μA
DC Current Gain	h <sub>FE</sub> (Note)	V <sub>CE</sub> =-6V, I <sub>C</sub> =-2mA	120	-	400	
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	I <sub>C</sub> =-100mA, I <sub>B</sub> =-10mA	-	-0.1	-0.3	V
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-1mA	80	-	-	MHz
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz	-	4.0	7.0	pF
Noise Figure	NF	V <sub>CE</sub> =-6V, I <sub>C</sub> =-0.1mA, f=1kHz, R <sub>g</sub> =10kΩ	-	1.0	10	dB

Note)h<sub>FE</sub> Classification : Y(4)120~240, GR(6)200~400

## Q<sub>2</sub> ELECTRICAL CHARACTERISTICS (Ta=25°C)

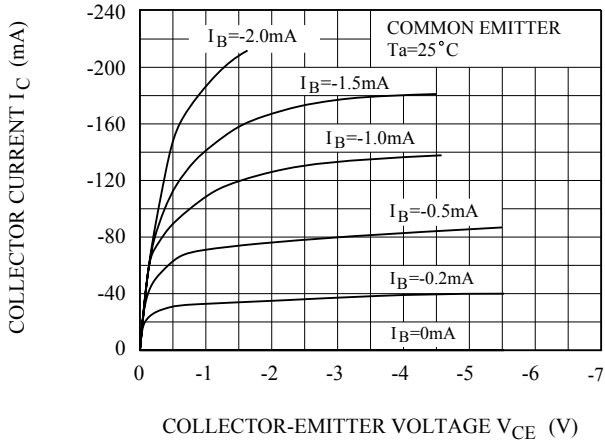
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT.
Collector Cut-off Current	I <sub>CB0</sub>	V <sub>CB</sub> =60V, I <sub>E</sub> =0	-	-	0.1	μA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0	-	-	0.1	μA
DC Current Gain	h <sub>FE</sub> (Note)	V <sub>CE</sub> =6V, I <sub>C</sub> =2mA	120	-	400	
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	I <sub>C</sub> =100mA, I <sub>B</sub> =10mA	-	0.1	0.25	V
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =1mA	80	-	-	MHz
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz	-	2.0	3.5	pF
Noise Figure	NF	V <sub>CE</sub> =6V, I <sub>C</sub> =0.1mA, f=1kHz, R <sub>g</sub> =10kΩ	-	1.0	10	dB

Note)h<sub>FE</sub> Classification : Y(4)120~240, GR(6)200~400

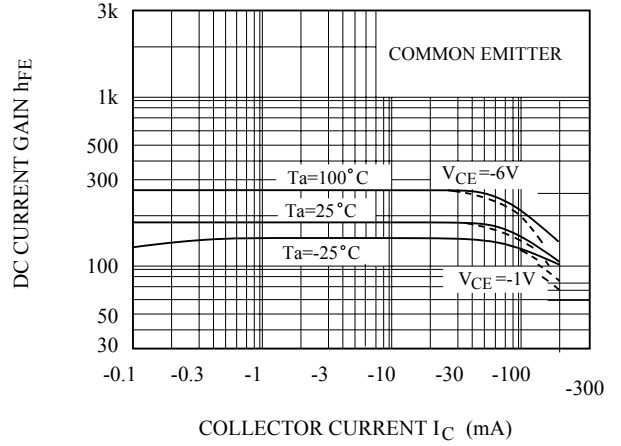
# KTX201E

## Q<sub>1</sub> (PNP TRANSISTOR)

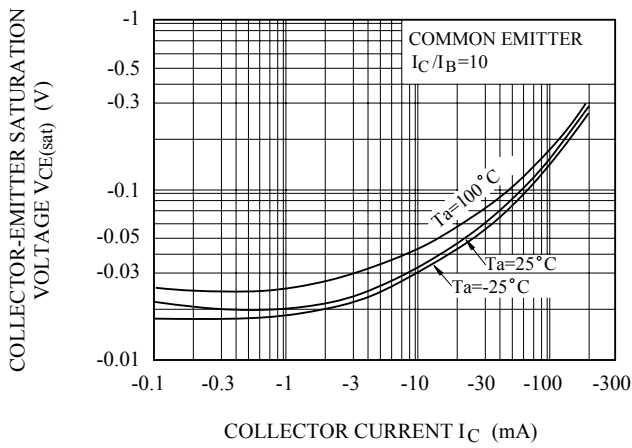
$I_C - V_{CE}$



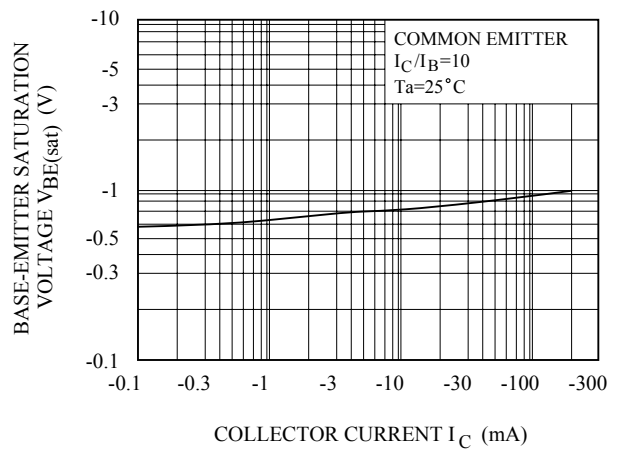
$h_{FE} - I_C$



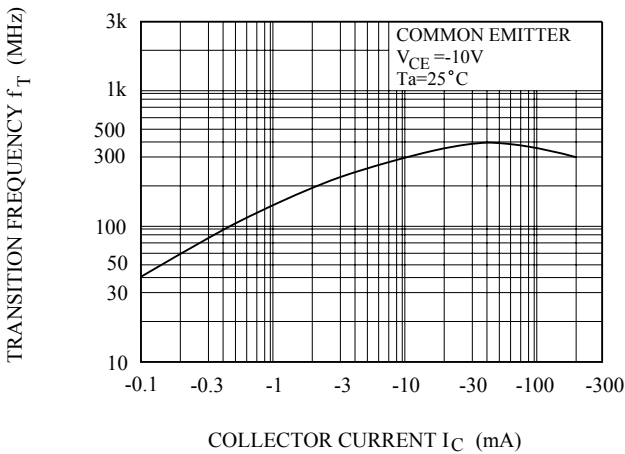
$V_{CE(sat)} - I_C$



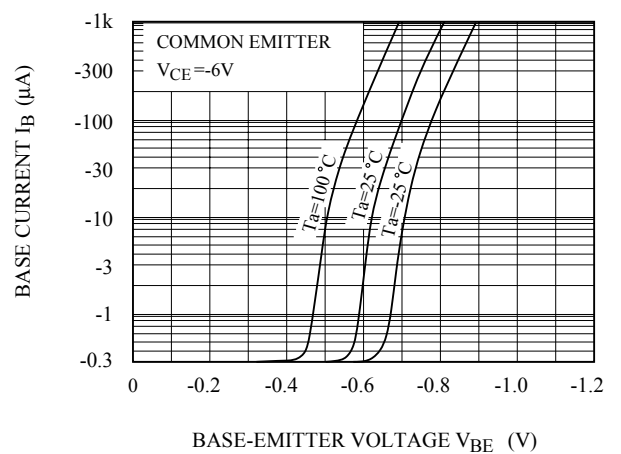
$V_{BE(sat)} - I_C$



$f_T - I_C$



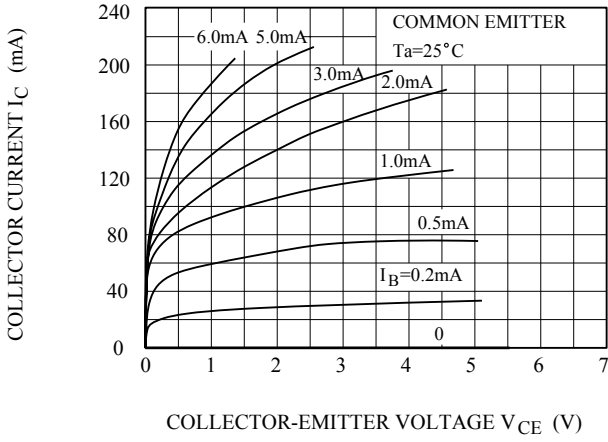
$I_B - V_{BE}$



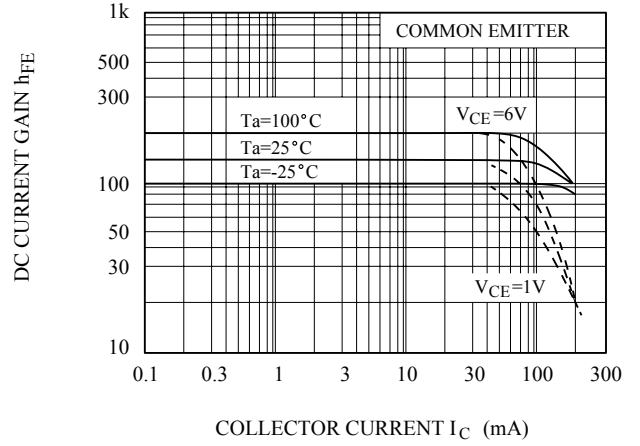
# KTX201E

## Q<sub>2</sub> (NPN TRANSISTOR)

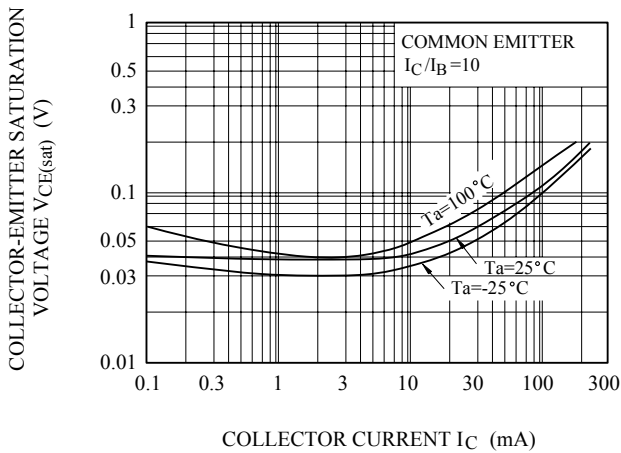
$I_C - V_{CE}$



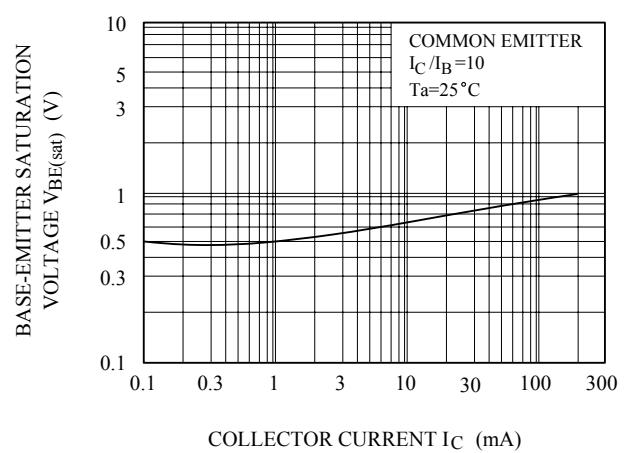
$h_{FE} - I_C$



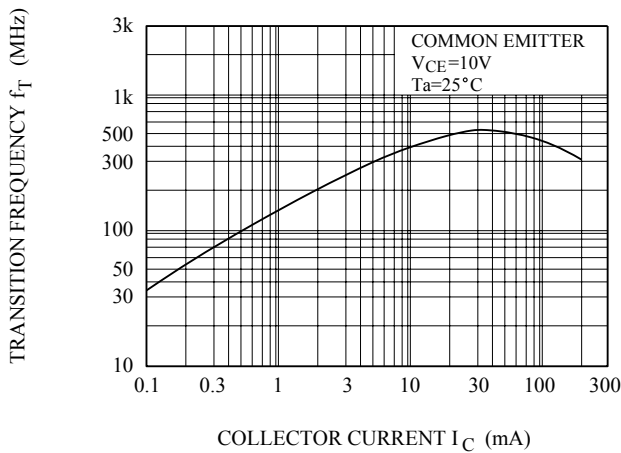
$V_{CE(sat)} - I_C$



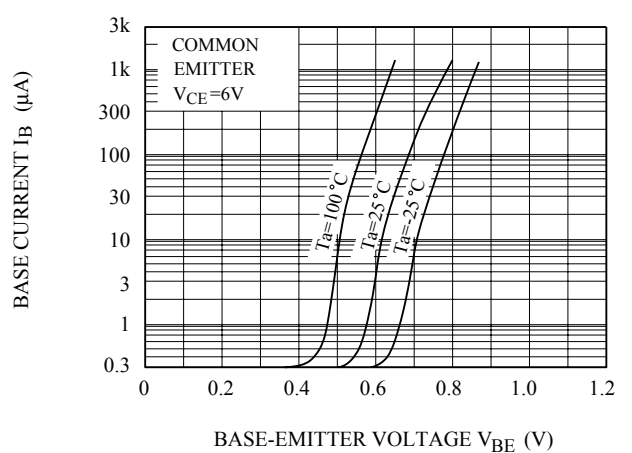
$V_{BE(sat)} - I_C$



$f_T - I_C$



$I_B - V_{BE}$



# KTX201E

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